AMENDMENTS

In the Specification:

Please amend paragraph [0005] as follows:

[0005] As a conventional AlGaAs semiconductor laser device, there is one as shown in Fig. 10 (see, e.g., JP 11-274644). The structure of the AlGaAs semiconductor laser device will be briefly described. As shown in Fig. 10, on an n-type GaAs substrate 501, there are an n-type GaAs buffer layer 502, an n-type $Al_{0.5}Ga_{0.5}As$ lower cladding layer ~~503~~ 504, an $Al_{0.35}Ga_{0.65}As$ lower guide layer ~~504~~ 503, a multiquantum well active layer 505 composed of two $Al_{0.12}Ga_{0.88}As$ well layers (each layer having a thickness of 80 Å) and three $Al_{0.35}Ga_{0.65}As$ barrier layers (each layer having a thickness of 50 Å) disposed alternately, an $Al_{0.35}Ga_{0.65}As$ upper guide layer 506, a p-type $Al_{0.5}Ga_{0.5}As$ first upper cladding layer 507 and a p-type GaAs etching stopper layer 508 that are stacked in this order. A mesa stripe-shaped p-type $Al_{0.5}Ga_{0.5}As$ second upper cladding layer 509 and an eaves-shaped p-type GaAs cap layer 510 are sequentially formed on a surface of the etching stopper layer 508. An n-type $Al_{0.3}Ga_{0.3}As$ first current blocking layer 511 and an n-type GaAs second current blocking layer 512 are stacked on both sides of the second upper cladding layer 509, so that regions other than the mesa stripe portion are defined as current constriction portions. A p-type GaAs planarizing layer 513 is formed on the second current blocking layer 512, and a p-type GaAs contact layer 514 is laid on the entire surface thereof.